

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Nobuhiko HAYASHI, et al.

Serial No.:

Group Art Unit:

Filed: February 28, 2002

Examiner:

For: NITRIDE-BASED SEMICONDUCTOR ELEMENT AND METHOD OF FORMING  
NITRIDE-BASED SEMICONDUCTOR

#3/105  
Rme  
5/1/02

11046 U.S. PTO  
10/084050



INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
Washington, DC 20231

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

Respectfully submitted,

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